

2SK360

Silicon N-Channel MOS FET

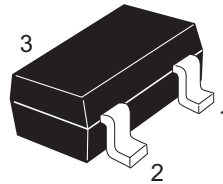
REJ03G0811-0200
(Previous ADE-208-1170)
Rev.2.00
Aug.10.2005

Application

VHF amplifier

Outline

RENESAS Package code: PLSP0003ZB-A
(Package name: MPAK)



1. Gate
2. Drain
3. Source

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSX}^{*1}	20	V
Gate to source voltage	V_{GSS}	±5	V
Drain current	I_D	30	mA
Gate current	I_G	±1	mA
Channel power dissipation	Pch	150	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. $V_{GS} = -4$ V

Electrical Characteristics

(Ta = 25°C)

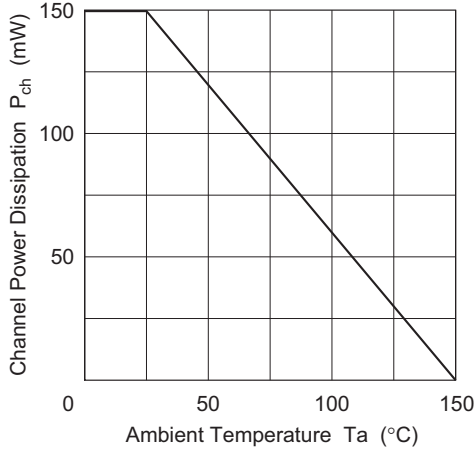
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSX}$	20	—	—	V	$I_D = 100 \mu A$, $V_{GS} = -4$ V
Gate cutoff current	I_{GSS}	—	—	±20	nA	$V_{GS} = \pm 5$ V, $V_{DS} = 0$
Drain current	I_{DSS}^{*1}	6	—	12	mA	$V_{DS} = 10$ V, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0	—	-2.0	V	$V_{DS} = 10$ V, $I_D = 10 \mu A$
Forward transfer admittance	$ y_{fs} $	8	14	—	mS	$V_{DS} = 10$ V, $V_{GS} = 0$, $f = 1$ kHz
Input capacitance	C_{iss}	—	2.5	—	pF	$V_{DS} = 10$ V, $V_{GS} = 0$, $f = 1$ MHz
Output capacitance	C_{oss}	—	1.6	—	pF	
Reverse transfer capacitance	C_{rss}	—	0.03	—	pF	
Power gain	PG	—	30	—	dB	$V_{DS} = 10$ V, $V_{GS} = 0$, $f = 100$ MHz
Noise figure	NF	—	2.0	—	dB	

Note: 1. The 2SK360 is grouped by I_{DSS} as follows.

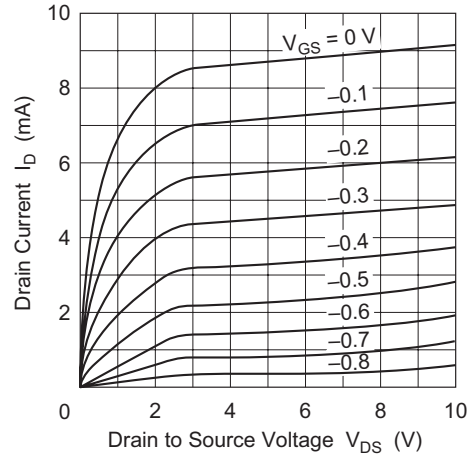
Grade	E	F
Mark	IGE	IGF
I_{DSS}	6 to 10	8 to 12

查询"2SK360IGETL"供应商

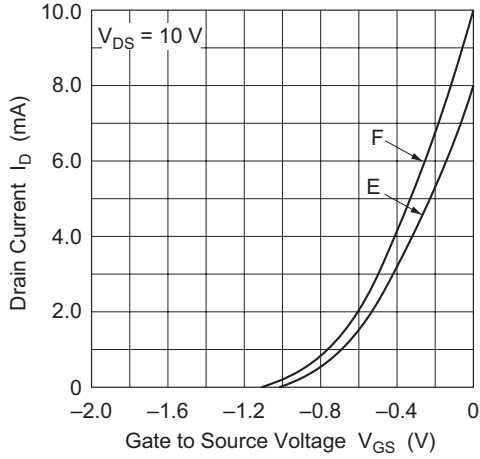
Maximum Channel Dissipation Curve



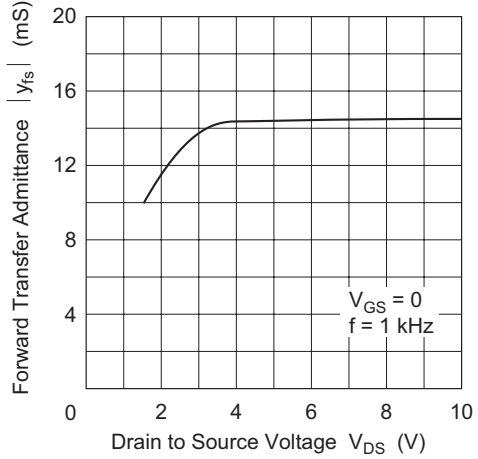
Typical Output Characteristics



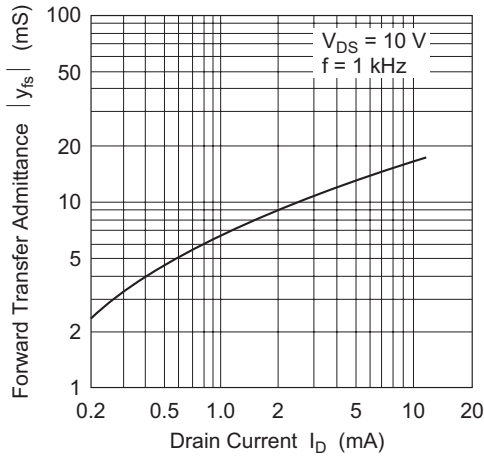
Typical Transfer Characteristics



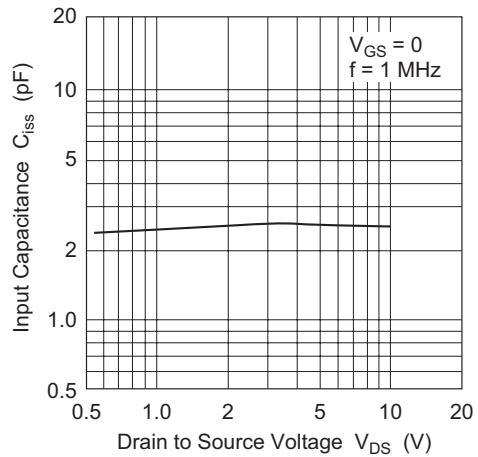
Forward Transfer Admittance vs. Drain to Source Voltage



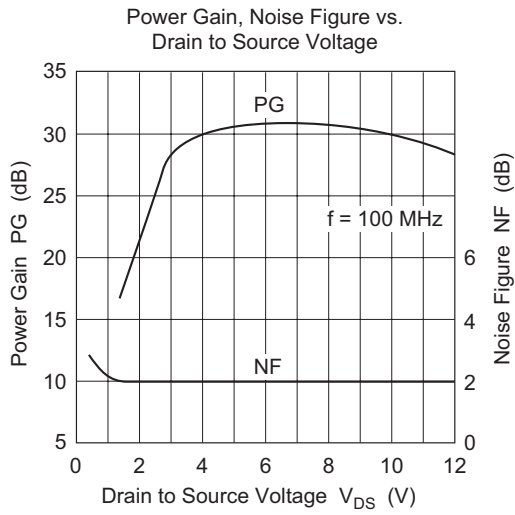
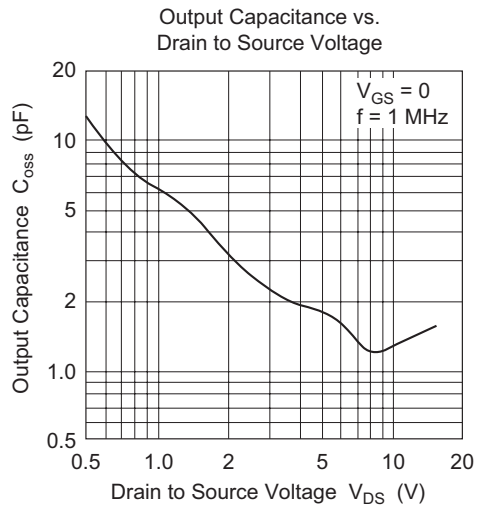
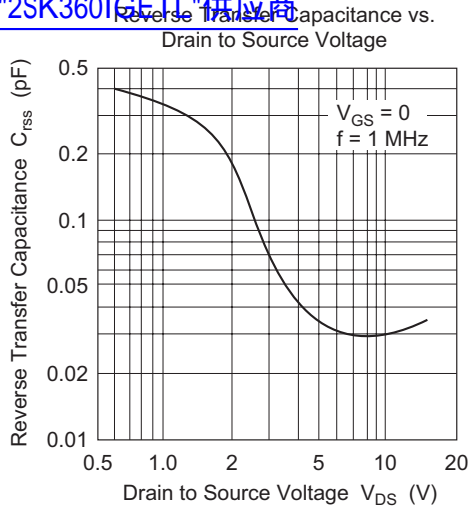
Forward Transfer Admittance vs. Drain Current



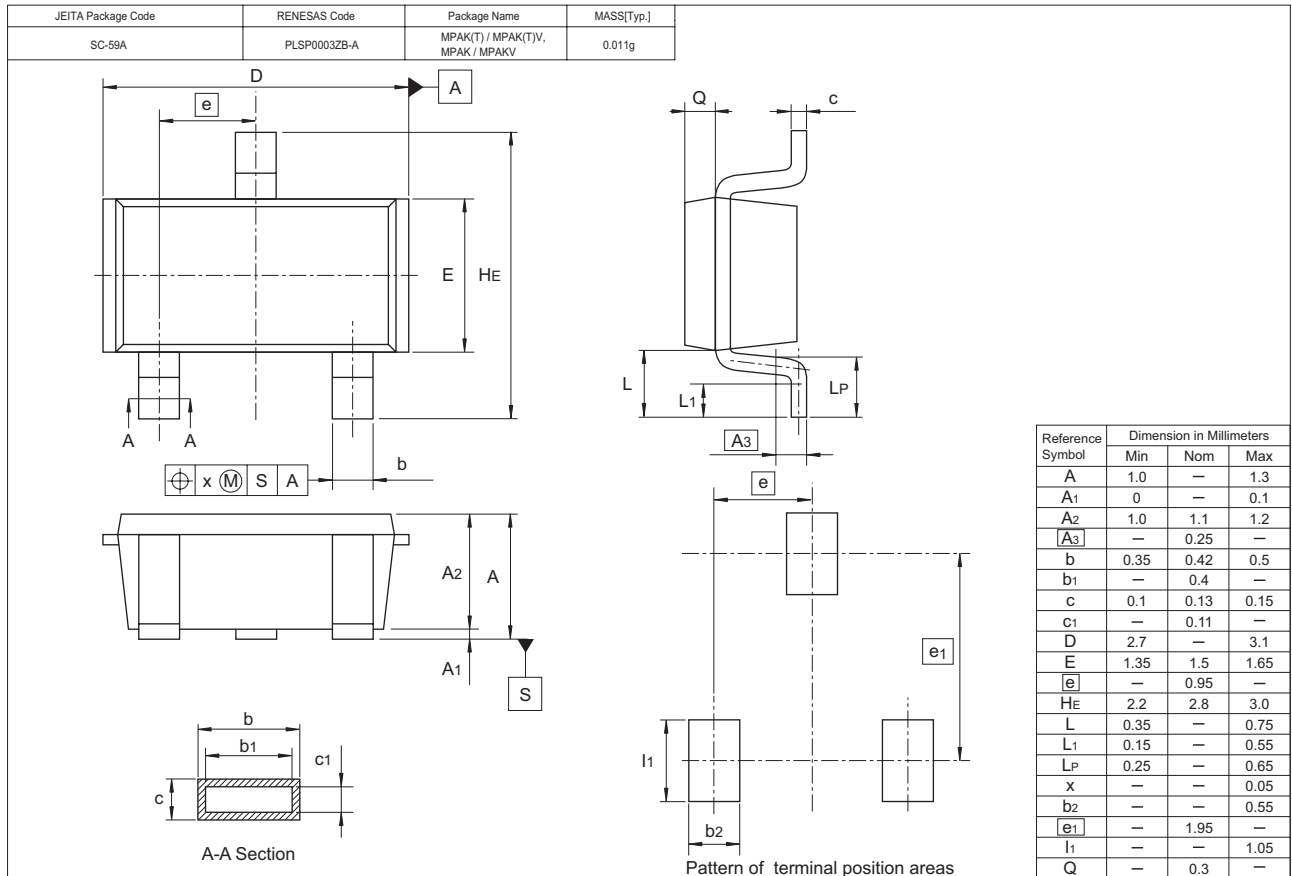
Input Capacitance vs. Drain to Source Voltage



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Part Name	Quantity	Shipping Container
2SK360IGETL	3000	φ178mm Reel , 8mm Emboss Taping
2SK360IGFTL	3000	φ178mm Reel , 8mm Emboss Taping

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Renesas Technology Hong Kong Ltd.

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Renesas Technology Taiwan Co., Ltd.

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Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
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Renesas Technology Singapore Pte. Ltd.

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Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
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